TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK1529

High-Power Amplifier Application

 $\begin{array}{ll} \bullet & \mbox{High breakdown voltage} & : \mbox{$V_{\rm DSS}$ = 180V} \\ \bullet & \mbox{High forward transfer admittance} & : \mbox{$|Y_{\rm fs}|$ = 4.0 S (typ.)} \\ \end{array}$

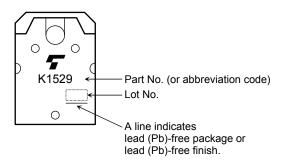
• Complementary to 2SJ200

Absolute Maximum Ratings (Ta = 25°C)

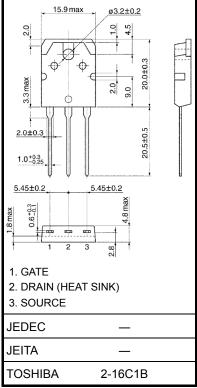
Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V_{DSS}	180	V	
Gate-source voltage	V_{GSS}	±20	V	
Drain current (Note 1)	ΙD	10	Α	
Drain power dissipation (Tc = 25°C)	P_{D}	120	W	
Channel temperature	T _c	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Marking



Unit: mm



Weight: 4.6 g (typ.)

Electrical Characteristics (Ta = 25°C)

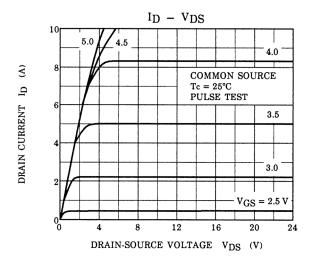
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} = 180 V, V _{GS} = 0	_	_	1.0	mA
Gate leakage current	I _{GSS}	V _{DS} = 0, V _{GS} = ±20 V	_	_	±0.5	μA
Drain-source breakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0	180	_	_	٧
Drain-source saturation voltage	V _{DS} (ON)	I _D = 6 A, V _{GS} = 10 V	_	2.5	5.0	V
Gate-source cut-off voltage (Note 2)	V _{GS} (OFF)	V _{DS} = 10 V, I _D = 0.1 A	0.8	_	2.8	٧
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3 A	_	4.0	_	S
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz	_	700	_	
Output capacitance	Coss	V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz	_	150	_	pF
Reverse transfer capacitance	C _{rss}	V _{DD} = 30 V, V _{GS} = 0, f = 1 MHz	_	90	_	

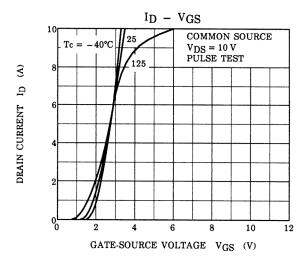
Note 1: Ensure that the channel temperature does not exceed 150°C.

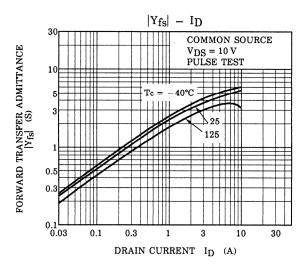
Note 2: V_{GS (OFF)} Classification 0: 0.8~1.6 Y: 1.4~2.8

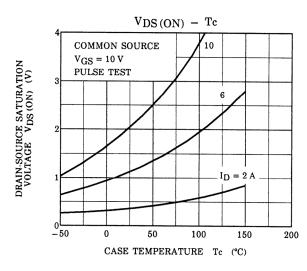
This transistor is an electrostatic-sensitive device.

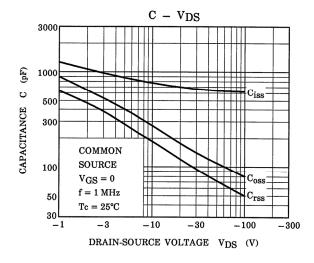
Please handle with caution.

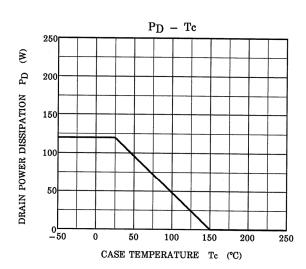


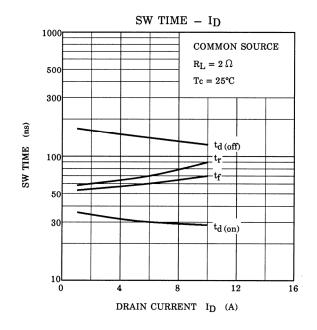


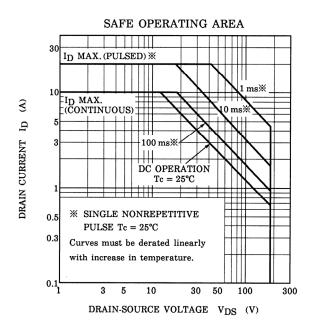




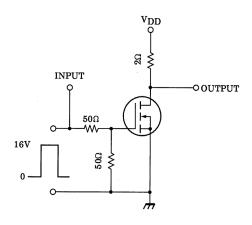




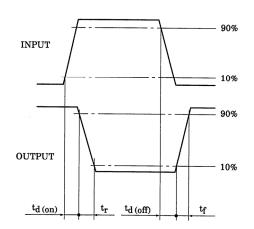




Switching Time Test Circuit



Waveforms



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